

## R-C Thermal Model Parameters

### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

*For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).*

### R-C THERMAL MODEL FOR TANK CONFIGURATION



<b>R-C VALUES FOR TANK CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	4.9420	976.8678 m	N/A
RT2	9.9325	682.8492 m	N/A
RT3	1.8410	1.6214	N/A
RT4	31.2845	918.8830 m	N/A
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	140.4427 m	11.7771 m	N/A
CT2	1.6022	4.0965	N/A
CT3	1.5539 m	68.1528 m	N/A
CT4	3.1588	591.3552 u	N/A

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*



## R-C THERMAL MODEL FOR FILTER CONFIGURATION



<b>R-C VALUES FOR FILTER CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RF1	1.7831	1.1279	N/A
RF2	5.8799	1.3511	N/A
RF3	17.1385	1.1481	N/A
RF4	23.1985	572.9000 m	N/A
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CF1	1.3806 m	608.7061 u	N/A
CF2	112.1216 m	13.9994 m	N/A
CF3	864.1544 m	94.5225 m	N/A
CF4	2.9415	5.3940	N/A

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

